Fabrication of omnidirectional photonic band gap structures for photonic devices in the near infrared and visible frequencies

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We describe the fabrication of a three dimensionally periodic crystal structure with omnidirectional band gap for devices in the near-IR and visible wavelength region using a technique of direct electron beam write coupled with multi-level alignment. This technique will allow us to fabricate prototype photonic band gap device structures with different materials in a direct way to test the effects of omnidirectional photonic gap on various optical phenomena (e.g. spontaneous emission, localization etc.). To demonstrate feasablility of this method we have successfully fabricated Iowa State "woodpile" structures with lattice spacings in the ~ 0.5 \Box m range. Prototype structures in the near –IR fabricated with silicon give a wide stop band in the stacking direction centered around 1.5 \Box m wavelength (figure 1) consistent with previously published structures. Woodpile structures fabricated with gold reveal a sharp band edge near ~ 1.0 \Box m wavelength with a broad high reflectivity region (close to 100%) for larger wavelengths. In this presentation we will describe the fabrication processes used and present optical characterization data from various structures.

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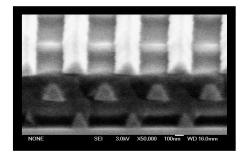


Figure 1.

